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Inventor Information for 10/791651

Inventor Name	City	State/Country				
OTSUKI, TETSUYA	JAPAN					
KUROSAWA, HIROFUMI	NAGANO-KEN	JAPAN				
MIKI, HIROSHI	NAGANO-KEN	JAPAN				
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US 20060165875 A1	20060727	INTERCONNECT SUBSTRATE, SEMICONDUCTOR DEVICE, METHODS OF MANUFACTURING THE SAME, CIRCUIT BOARD, AND ELECTRONIC EQUIPMENT	427/58	427/258; 427/402	Otsuki; Tetsuya
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US 20060103788 A1	20060518	Method for mounting electronic element, method for producing electronic device, circuit board, and electronic instrument	349/110	174/262; 29/832; 349/111	Kurosawa; Hirofumi et al.
US 20060103000 A1	20060518	Electronic device package and electronic equipment	257/690		Kurosawa; Hirofumi
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US 20040222889 A1	20041111	Contactless data communication system, contactless identification tag and contactless identification tag control program	340/572.8		Hoshina, Masaki et al.
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